MOSFETs Silicon N-channel MOS (U-MOSIX-H)

# TPH3R003PL

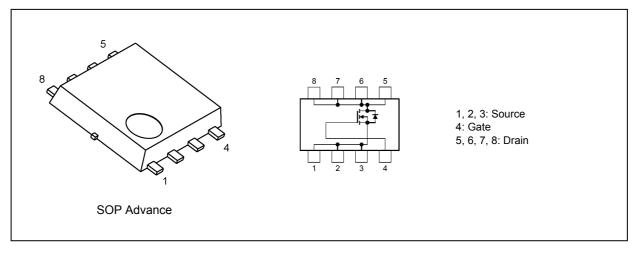
#### 1. Applications

- High-Efficiency DC-DC Converters
- Switching Voltage Regulators
- Motor Drivers

#### 2. Features

- (1) High-speed switching
- (2) Small gate charge:  $Q_{SW} = 13 \text{ nC}$  (typ.)
- (3) Small output charge:  $Q_{oss} = 24 \text{ nC}$  (typ.)
- (4) Low drain-source on-resistance:  $R_{DS(ON)} = 2.2 \text{ m}\Omega$  (typ.) ( $V_{GS} = 10 \text{ V}$ )
- (5) Low leakage current:  $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 30 \ V)$
- (6) Enhancement mode:  $V_{th}$  = 1.1 to 2.1 V ( $V_{DS}$  = 10 V,  $I_D$  = 0.3 mA)

#### 3. Packaging and Internal Circuit



#### 4. Absolute Maximum Ratings (Note) ( $T_a = 25 \text{ °C}$ unless otherwise specified)

Characteris	Symbol	Rating	Unit		
Drain-source voltage			V <sub>DSS</sub>	30	V
Gate-source voltage		(Note 1)	V <sub>GSS</sub>	±20	
Drain current (DC)	( T <sub>c</sub> = 25 °C )	(Note 2)	Ι <sub>D</sub>	88	A
Drain current (DC)	(Silicon limit)	(Note 2), (Note 3)	Ι <sub>D</sub>	134	
Drain current (pulsed)	(t = 100 µs)	(Note 2)	I <sub>DP</sub>	200	
Power dissipation	( T <sub>c</sub> = 25 °C )		PD	90	w
Power dissipation		(Note 4)	PD	1.8	
Power dissipation		(Note 5)	PD	0.83	
Single-pulse avalanche energy		(Note 6)	E <sub>AS</sub>	30	mJ
Single-pulse avalanche current		(Note 6)	I <sub>AS</sub>	88	A
Channel temperature			T <sub>ch</sub>	175	°C
Storage temperature			T <sub>stg</sub>	-55 to 175	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit		
Channel-to-case thermal resistance	( T <sub>c</sub> = 25 °C )		R <sub>th(ch-c)</sub>	1.66	°C/W
Channel-to-ambient thermal resistance	( T <sub>a</sub> = 25 °C )	(Note 4)	R <sub>th(ch-a)</sub>	83	
Channel-to-ambient thermal resistance	( T <sub>a</sub> = 25 °C )	(Note 5)	R <sub>th(ch-a)</sub>	180	

Note 1: +20 V/-16 V ensured at DC condition.

-20 V ensured at pulse condition (duty 5 %).

Note 2: Ensure that the channel temperature does not exceed 175 °C.

Note 3: Limited 88 A by package capability.

Note 4: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 5: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 6: V<sub>DD</sub> = 24 V, T<sub>ch</sub> = 25 °C (initial), L = 3.0  $\mu$ H, I<sub>AS</sub> = 88 A

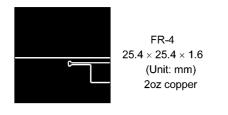
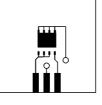


Fig. 5.1 Device Mounted on a Glass-Epoxy

Board (a)



FR-4 25.4 × 25.4 × 1.6 (Unit: mm) 2oz copper



Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

#### 6. Electrical Characteristics

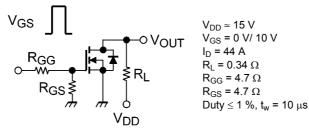
#### 6.1. Static Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±20 V, $V_{DS}$ = 0 V	_	_	±0.1	μA
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V			10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	30	—	_	V
Drain-source breakdown voltage (Note 7)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V	15		_	
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.3 mA	1.1		2.1	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 44 A	_	2.9	4.2	mΩ
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 44 A	_	2.2	3.0	

Note 7: If a reverse bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drainsource breakdown voltage is lowered in this mode.

#### 6.2. Dynamic Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	2940	3825	pF
Reverse transfer capacitance	C <sub>rss</sub>		_	88	165	
Output capacitance	C <sub>oss</sub>		_	850	—	
Gate resistance	r <sub>g</sub>	—		1.0	1.5	Ω
Switching time (rise time)	tr	See Figure 6.2.1	_	6.3	—	ns
Switching time (turn-on time)	t <sub>on</sub>		_	18	_	
Switching time (fall time)	t <sub>f</sub>		_	5.9	_	
Switching time (turn-off time)	t <sub>off</sub>			36	_	



#### Fig. 6.2.1 Switching Time Test Circuit

#### 6.3. Gate Charge Characteristics ( $T_a = 25$ °C unless otherwise specified)

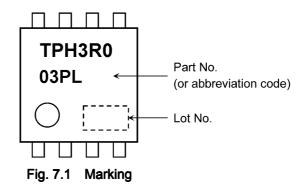
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus	Qg	$V_{DD}\approx 15 \text{ V}, \text{ V}_{GS} \text{ = } 10 \text{ V}, \text{ I}_{D} \text{ = } 44 \text{ A}$	_	50	_	nC
gate-drain)		$V_{DD} \approx 15 \text{ V}, \text{ V}_{GS}$ = 4.5 V, I <sub>D</sub> = 44 A	_	24	_	
Gate-source charge 1	Q <sub>gs1</sub>	$V_{DD} \approx 15 \text{ V}, \text{ V}_{GS}$ = 10 V, I <sub>D</sub> = 44 A	_	10	—	
Gate-drain charge	Q <sub>gd</sub>		_	7.8	_	
Gate switch charge	Q <sub>SW</sub>		—	13	_	
Output charge	Q <sub>oss</sub>	$V_{DS}$ = 15 V, $V_{GS}$ = 0 V, f = 1 MHz		24		

### 6.4. Source-Drain Characteristics ( $T_a = 25$ °C unless otherwise specified)

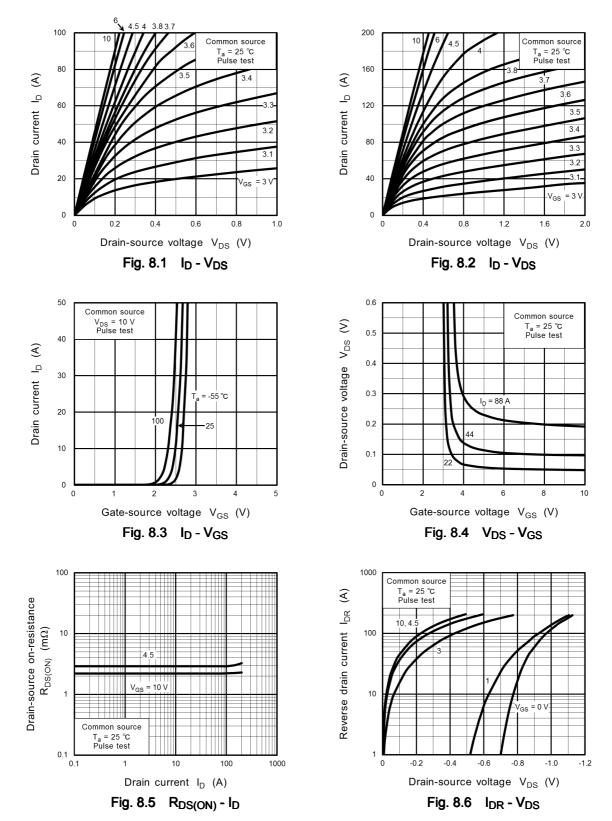
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (Note 8)	I <sub>DRP</sub>	(t = 100 μs)	_	—	200	А
Diode forward voltage	V <sub>DSF</sub>	I <sub>DR</sub> = 88 A, V <sub>GS</sub> = 0 V			-1.2	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 22 A, V <sub>GS</sub> = 0 V,	_	34	_	ns
Reverse recovery charge	Q <sub>rr</sub>	-dl <sub>DR</sub> /dt = 100 A/μs	_	25	_	nC

Note 8: Ensure that the channel temperature does not exceed 175 °C.

#### 7. Marking



#### 8. Characteristics Curves (Note)



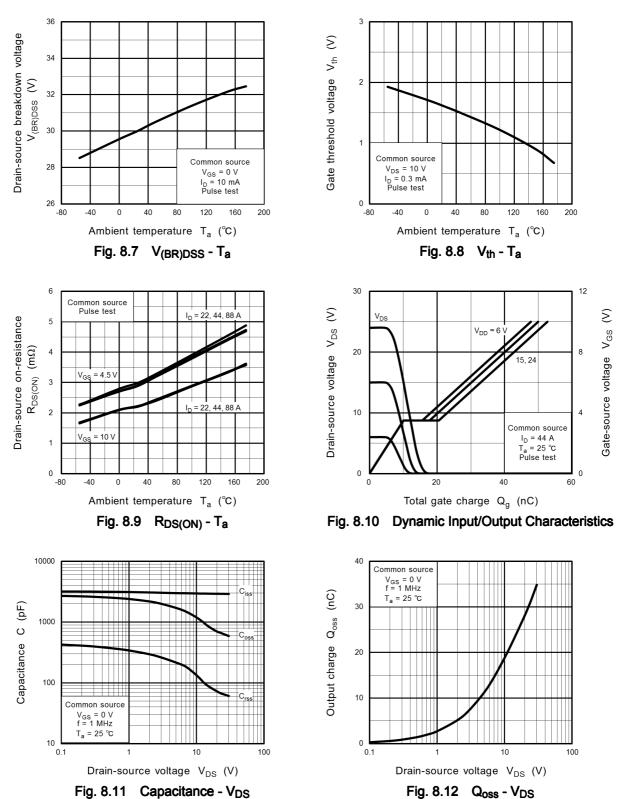
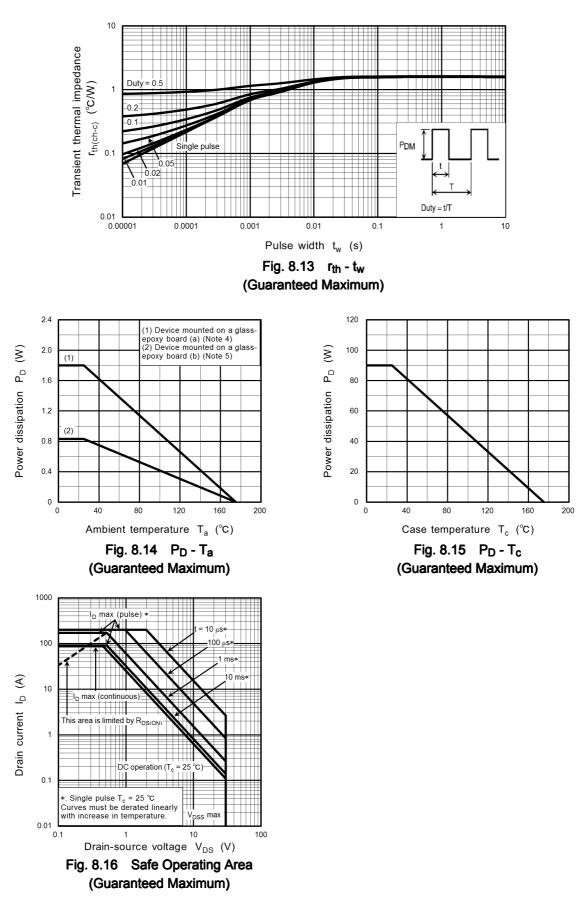


Fig. 8.11 Capacitance - V<sub>DS</sub>



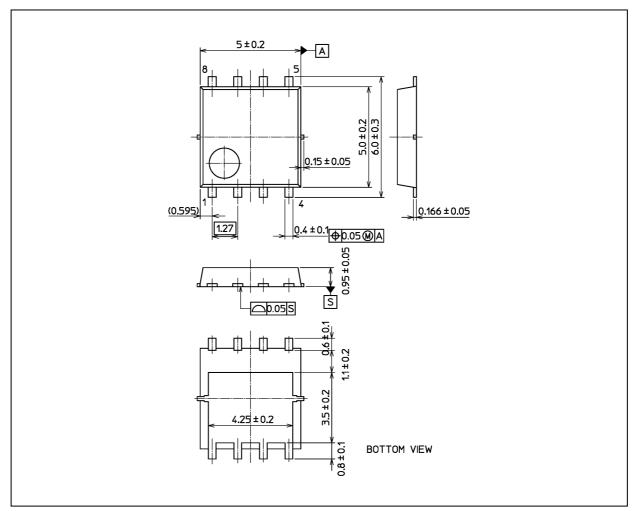
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### TPH3R003PL

#### Package Dimensions

Unit: mm



Weight: 0.069 g (typ.)

TOSHIBA: 2-5Q1S

Nickname: SOP Advance

Package Name(s)

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